

CORRECTION

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Correction to: Wafer-Scale Fabrication of Sub-10 nm TiO₂-Ga₂O₃ n-p Heterojunctions with Efficient Photocatalytic Activity by Atomic Layer Deposition

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Please be advised that the name of one of the coauthors in the original article [1] has been incorrectly spelled: '*Ranish M. Ramachandran*' should be '*Ranjith K. Ramachandran*'.

The authors apologize for this error.

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1. Xu et al (2019) Wafer-Scale Fabrication of Sub-10 nm TiO₂-Ga₂O₃ n-p Heterojunctions with Efficient Photocatalytic Activity by Atomic Layer Deposition. *Nanoscale Res Lett* 14:163. <https://doi.org/10.1186/s11671-019-2991-1>

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